



# SLOVENSKI STANDARD

## SIST EN 62562:2011

01-april-2011

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### Metoda z votlinskim resonatorjem za merjenje kompleksne permitivnosti nizkoizgubnih dielektričnih plošč (IEC 62562:2010)

Cavity resonator method to measure the complex permittivity of low-loss dielectric plates (IEC 62562:2010)

Hohlraumresonanzverfahren zum Messen der komplexen Permittivität von verlustarmen dielektrischen Platten (IEC 62562:2010)

Méthode de la cavité résonante pour mesurer la permittivité complexe des plaques diélectriques à faibles pertes (CEI 62562:2010)

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Ta slovenski standard je istoveten z: EN 62562:2011

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#### **ICS:**

17.220.20	Merjenje električnih in magnetnih veličin	Measurement of electrical and magnetic quantities
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**SIST EN 62562:2011**

**en**

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EUROPEAN STANDARD  
NORME EUROPÉENNE  
EUROPÄISCHE NORM

**EN 62562**

February 2011

ICS 17.220

English version

**Cavity resonator method to measure the complex permittivity  
of low-loss dielectric plates  
(IEC 62562:2010)**

Méthode de la cavité résonante pour  
mesurer la permittivité complexe des  
plaques diélectriques à faibles pertes  
(CEI 62562:2010)

Hohlraumresonanzverfahren zum Messen  
der komplexen Permittivität von  
verlustarmen dielektrischen Platten  
(IEC 62562:2010)

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European Committee for Electrotechnical Standardization  
Comité Européen de Normalisation Electrotechnique  
Europäisches Komitee für Elektrotechnische Normung

**Management Centre: Avenue Marnix 17, B - 1000 Brussels**

## Foreword

The text of document 46F/118/CDV, future edition 1 of IEC 62562, prepared by SC 46F, R.F. and microwave passive components, of IEC TC 46, Cables, wires, waveguides, R.F. connectors, R.F. and microwave passive components and accessories, was submitted to the IEC-CENELEC parallel vote and was approved by CENELEC as EN 62562 on 2011-01-02.

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- latest date by which the EN has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2011-10-02
- latest date by which the national standards conflicting with the EN have to be withdrawn (dow) 2014-01-02

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IEC 62562

Edition 1.0 2010-02

# INTERNATIONAL STANDARD



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**Cavity resonator method to measure the complex permittivity of low-loss dielectric plates**

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INTERNATIONAL  
ELECTROTECHNICAL  
COMMISSION

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## INTERNATIONAL ELECTROTECHNICAL COMMISSION

## CAVITY RESONATOR METHOD TO MEASURE THE COMPLEX PERMITTIVITY OF LOW-LOSS DIELECTRIC PLATES

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International Standard IEC 62562 has been prepared by subcommittee 46F: R.F. and microwave passive components, of IEC technical committee 46: Cables, wires, waveguides, R.F. connectors, R.F. and microwave passive components and accessories.

This first edition cancels and replaces the PAS published in 2008.

The text of this standard is based on the following documents:

CDV	Report on voting
46F/118/CDV	46F/143/RVC

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

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## CAVITY RESONATOR METHOD TO MEASURE THE COMPLEX PERMITTIVITY OF LOW-LOSS DIELECTRIC PLATES

### 1 Scope

The object of this International Standard is to describe a measurement method of dielectric properties in the planar direction of dielectric plate at microwave frequency. This method is called a cavity resonator method. It has been created in order to develop new materials and to design microwave active and passive devices for which standardization of measurement methods of material properties is more and more important.

This method has the following characteristics:

- the relative permittivity  $\epsilon'$  and loss tangent  $\tan \delta$  values of a dielectric plate sample can be measured accurately and non-destructively;
- temperature dependence of complex permittivity can be measured;
- the measurement accuracy is within 0,3 % for  $\epsilon'$  and within  $5 \times 10^{-6}$  for  $\tan \delta$ ;
- fringing effect is corrected using correction charts calculated on the basis of rigorous analysis.

This method is applicable for the measurements on the following condition:

- frequency : 2 GHz <  $f$  < 40 GHz;
- relative permittivity: 2 <  $\epsilon'$  < 100;
- loss tangent :  $10^{-6}$  <  $\tan \delta$  <  $10^{-2}$

### 2 Measurement parameters

The measurement parameters are defined as follows:

$$\epsilon_r = \epsilon' - j\epsilon'' = D/(\epsilon_0 E) \quad (1)$$

$$\tan \delta = \epsilon'' / \epsilon' \quad (2)$$

$$TC\epsilon = \frac{1}{\epsilon_{\text{ref}}} \frac{\epsilon_T - \epsilon_{\text{ref}}}{T - T_{\text{ref}}} \times 10^6 \quad (1 \times 10^{-6}/\text{K}) \quad (3)$$

where

- $D$  is the electric flux density;
- $E$  is the electric field strength;
- $\epsilon_0$  is the permittivity in a vacuum;
- $\epsilon'$  and  $\epsilon''$  are the real and imaginary components of the complex relative permittivity  $\epsilon_r$ ;
- $TC\epsilon$  is the temperature coefficient of relative permittivity;
- $\epsilon_T$  and  $\epsilon_{\text{ref}}$  are the real parts of the complex relative permittivity at temperature  $T$  and reference temperature  $T_{\text{ref}}$  (= 20 °C to 25 °C), respectively.

### 3 Theory and calculation equations

#### 3.1 Relative permittivity and loss tangent

A resonator structure used in the nondestructive measurement of the complex permittivity is shown in Figure 1a.

A cavity having diameter  $D$  and length  $H = 2M$  is cut into two halves in the middle of its length.

A dielectric plate sample having  $\varepsilon'$ ,  $\tan\delta$  and thickness  $t$  is placed between these two halves.

The  $TE_{011}$  mode, having only the electric field component tangential to the plane of the sample, is used for the measurement, since air gaps at the plate-cavity interfaces do not affect the electromagnetic field. Taking account of the fringing field in the plate region outside diameter of the cavity on the basis of the rigorous mode matching analysis, we determine  $\varepsilon'$  and  $\tan\delta$  from the measured values of the resonant frequency  $f_0$  and the unloaded Q-factor  $Q_u$ . This numerical calculation, however, is rather tedious.

Therefore,

- approximated values  $\varepsilon'_a$  and  $\tan\delta_a$  from the  $f_0$  and  $Q_u$  values by using simple formula for a resonator structure shown in Figure 1b, where a fringing effect for Figure 1a is neglected, will be determined;
- then, accurate values  $\varepsilon'$  and  $\tan\delta$  from  $\varepsilon'_a$  and  $\tan\delta_a$  using charts calculated from the rigorous analysis will be obtained.

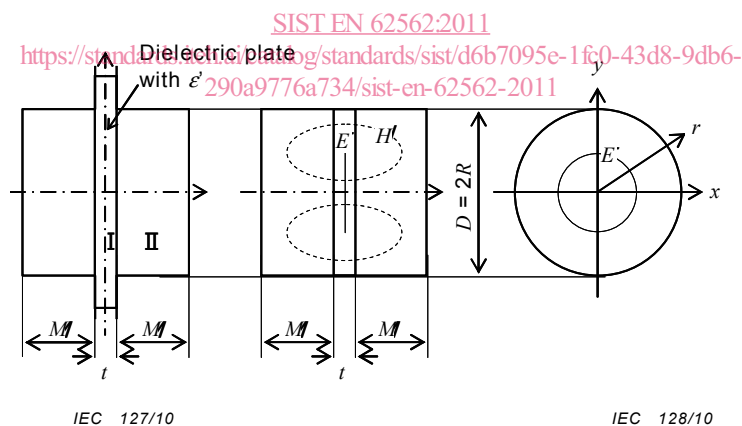


Figure 1a – Resonator used in measurement    Figure 1b – Resonator to calculate  $\varepsilon'_a$  and  $\tan\delta_a$

Figure 1 – Resonator structures of two types

The value of  $\varepsilon'_a$  is given by

$$\varepsilon'_a = \left( \frac{c}{\pi t f_0} \right)^2 \left\{ X^2 - Y^2 \left( \frac{t}{2M} \right)^2 \right\} + 1 \quad (4)$$

where  $c$  is the velocity of light in a vacuum ( $c = 2,9979 \times 10^8$  m/s) and the first root  $X$  is

calculated from a given value  $Y$ , using the following simultaneous equations:

$$X \tan X = \frac{t}{2M} Y \cot Y \quad (5)$$

$$Y = M \sqrt{k_0^2 - k_r^2} = jY' \quad (6)$$

with  $k_0 = 2\pi f_0/c$ ,  $k_r = j'_{01}/R$ , and  $j'_{01} = 3,83173$  for the  $TE_{011}$  mode. When  $k_0 - k_r < 0$ ,  $Y$  is replaced by  $jY'$ .

The value of  $\tan \delta_a$  is given by

$$\tan \delta_a = \frac{A}{Q_u} - R_s B \quad (7)$$

where  $R_s$  is the surface resistance of the conductor of cavity, given by

$$R_s = \sqrt{\frac{\pi f_0 \mu}{\sigma}} \quad (1/S), \quad \sigma = \sigma_0 \sigma_r \quad (S/m) \quad (8)$$

Here,  $\mu$  and  $\sigma$  are the permeability and conductivity of the conductor. Furthermore,  $\sigma_r$  is the relative conductivity and  $\sigma_0 = 5,8 \times 10^7$  S/m is the conductivity of standard copper. Constants  $A$  and  $B$  are given by

$$A = 1 + \frac{W_2^e}{W_1^e} \quad (9)$$

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$$B = \frac{P_{cy1} + P_{cy2} + P_{end}}{\omega R_s W_1^e} \quad (10)$$

In the above,  $W_1^e$  and  $W_2^e$  are electric field energies stored in the dielectric plate of region 1 and air of region 2 shown in Figure 1a. Furthermore,  $P_{cy1}$ ,  $P_{cy2}$  and  $P_{end}$  are the conductor loss at the cylindrical wall in the region 1, 2 and at the end wall. These parameters are given by

$$W_1^e = \frac{\pi}{8} \varepsilon_0 \varepsilon'_a \mu_0^2 \omega^2 j_{01}'^2 J_0^2(j'_{01}) t \left( 1 + \frac{\sin 2X}{2X} \right) \quad (11)$$

$$W_2^e = \frac{\pi}{4} \varepsilon_0 \mu_0^2 \omega^2 j_{01}'^2 J_0^2(j'_{01}) M \left( 1 - \frac{\sin 2Y}{2Y} \right) \frac{\cos^2 X}{\sin^2 Y} \quad (12)$$

$$P_{cy1} = \frac{\pi}{4} R_s J_0^2(j'_{01}) t R k_r^4 \left( 1 + \frac{\sin 2X}{2X} \right) \quad (13)$$

$$P_{cy2} = \frac{\pi}{2} R_s J_0^2(j'_{01}) M R k_r^4 \left( 1 - \frac{\sin 2Y}{2Y} \right) \frac{\cos^2 X}{\sin^2 Y} \quad (14)$$